

isc Silicon PNP Power Transistor

2SA940

DESCRIPTION

- Collector-Emitter Breakdown Voltage
: $V_{(BR)CEO} = -150V(\text{Min})$
- DC Current Gain
: $h_{FE} = 40-140 @ I_C = -0.5A$
- Complement to Type 2SC2073
- 100% tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

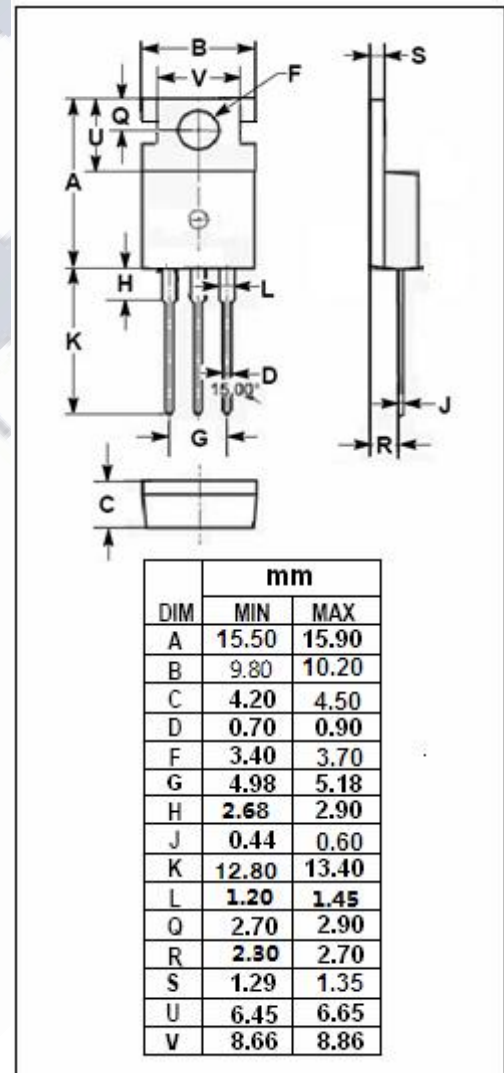
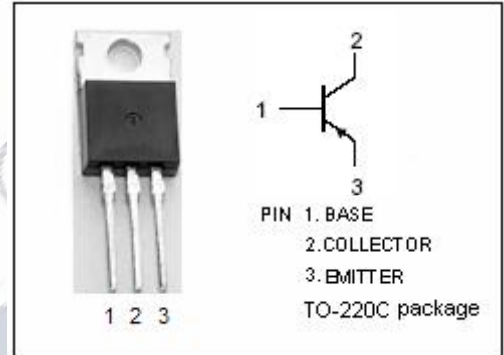
- Designed for use in general purpose power amplifier , vertical output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
P_C	Total Power Dissipation @ $T_C=25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	5.0	$^\circ\text{C/W}$



isc Silicon PNP Power Transistor**2SA940****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA ; I _B = 0	-150			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA ; I _E = 0	-150			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA ; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A ; I _B = -50mA			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -0.5A ; V _{CE} = -10V			-0.85	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V ; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V ; I _C = 0			-10	μ A
h _{FE}	DC Current Gain	I _C = -0.5A ; V _{CE} = -10V	40		140	
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A ; V _{CE} = -10V ; f _{test} = 1MHz		4		MHz